Optical excitation spectrum of an atom in a surface-induced potential

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We study the optical excitation spectrum of an atom in the vicinity of a dielectric surface. We calculate the rates of the total scattering and the scattering into the evanescent modes. With a proper assessment of the limitations, we demonstrate the portability of the at-surface results to an experimental situation with a nanober. The elect of the surface-induced potential on the excitation spectrum for free-to-bound transitions is shown to be weak. On the contrary, the elect for bound-to-bound transitions is signicant leading to a large excitation linewidth, a substantial negative shift of the peak position, and a strong long tail on the negative side and a small short tail on the positive side of the eld (atom frequency detuning.

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The study of individual neutral atoms in the vicinity of dielectric and metal surfaces has gained renewed interest due to progress in atom optics and nanotechnology [1, 2, 3, 4, 5, 6, 7]. The ability of manipulating atoms near surfaces has established them as a tool for cutting-edge applications such as quantum computation [8, 9, 10], atom chips [11, 12], and probes, very sensitive to the surface-induced perturbations [13]. Recently, translational levels of an atom in a surface—induced po tential have been studied [1, 2, 3, 4]. An optical technique for loading atoms into quantum adsorption states of a dielectric surface has been suggested [1, 2]. An experim ental observation of the excitation spectrum of cesium atoms in quantum adsorption states of a nano ber surface has been reported [3]. Spontaneous radiative decay oftranslational levels of an atom near a dielectric surface has been investigated [4]. In this paper, we study the optical excitation spectrum of an atom in a surface-induced potential.

We assume the whole space to be divided into two regions, namely, the half-space x < 0, occupied by a nondispersive nonabsorbing dielectric medium (medium 1), and the half-space x > 0, occupied by vacuum (medium 2). We exam ine an atom, with an upper internal levele and a lower internal level g, moving in the empty half-space x > 0.

The potential energy of the surface {atom interaction is a combination of a long-range van der W aals attraction $C_3=x^3$ and a short-range repulsion [14]. Here C_3 is the van der W aals coe cient. We approximate the short-range repulsion by an exponential function Ae^{-x} , where the parameters A and determine the height and range, respectively, of the repulsion. The combined potential depends on the internal state of the atom (see Fig. 1), and is presented in the form $V_j(x) = A_j e^{-jx} - C_{3j} = x^3$, where j=e or g labels the internal state of the atom. The potential parameters C_{3j} , A_j , and j depend on the dielectric and the atom. In numerical calculations, we use the parameters of fused silica, for the dielectric, and the parameters of atom ic cesium with the D_2 line, for the two-level atom ic model. A coording to Ref. [4], the

param eters of the ground—and excited–state potentials for the silica {cesium interaction are C $_{3g}=1.56$ kH z m 3 , C $_{3e}=3.09$ kH z m 3 , A $_g=1.6$ 10^{18} H z, A $_e=3.17$ 10^{18} H z, and $_g=_e=53$ nm 1 .

W e introduce the notation ' $_{\rm a}$ ' $_{\rm e}$ and ' $_{\rm b}$ ' $_{\rm g}$ for the eigenfunctions of the center-of-m ass motion of the atom in the potentials $V_{\rm e}$ and $V_{\rm g}$, respectively. They are determined by the stationary Schrödinger equations

$$\frac{h^2}{2m} \frac{d^2}{dx^2} + V_j(x) \quad '_j(x) = E_j'_j(x):$$
 (1)

Herem is the mass of the atom. The eigenvalues E_a E_e and E_b E_g are the total center-of-mass energies of the translational levels of the excited and ground states, respectively. These eigenvalues are the shifts of the energies of the translational levels from the energies of the corresponding internal states. Without the loss of generality, we assume that the center-of-mass eigenfunctions 'a and 'b are real functions.

FIG. 1: Energies and wave functions of the center-ofm ass motion of the ground-and excited-state atoms in the surface-induced potentials. The parameters of the potentials are C $_{3g}=1.56~\rm kH~z$ m 3 , C $_{3e}=3.09~\rm kH~z$ m 3 , A $_{g}=1.6$ $10^{-18}~\rm H~z$, A $_{e}=3.17$ $10^{-18}~\rm H~z$, and $_{g}=_{e}=53~\rm nm$ $^{-1}$. The mass of atom ic cesium m = 132.9 a.u. is used. We plot, for the excited state, two bound levels (= 400 and 415) and, for the ground state, two bound levels (= 281 and 285) and one free level (E $_{f}=4.25~\rm M~H~z)$.

We introduce the combined eigenstates $jai = jei \quad j_ai$ and $joi = jgi \quad j_bi$, which are formed from the internal and translational eigenstates. The corresponding energies are $h!_a = h!_e + E_a$ and $h!_b = h!_g + E_b$. Here, $!_j$ with j = e or g is the frequency of the internal level j. Then, the H am iltonian of the atom moving in the surface-induced potential can be represented in the diagonal form $H_A = {}_a h!_a jaihaj + {}_b h!_b jbihoj$. We emphasize that the sum mations over a and b include both the discrete

 $(\!E_{a\,;b}<\,0)$ and continuous $(\!E_{a\,;b}>\,0)$ spectra. The levels a with $E_a < 0$ and the levels bwith $E_b < 0$ are called the bound (or vibrational) levels of the excited and ground states, respectively. In such a state, the atom is bound to the surface. It is vibrating, or more exactly, moving back and forth between the walls formed by the van der W aals potential and the repulsion potential. The levels a with $E_a > 0$ and the levels b with $E_b > 0$ are called the free (or continuum) levels of the excited and ground states, respectively. The center-of-mass wave functions of the bound levels are normalized to unity. The centerof-m ass wave functions of the free levels are normalized to the delta function of energy. For bound states, the center-of-m asswave functions ' a and ' b can be labeled by the quantum numbers a and b, respectively. For free levels, the conventional sum s over a and b m ust be replaced by the integrals over E_a and E_b , respectively.

Suppose that the atom is driven by a coherent planewave laser eld E $_1$ = [Ee $^{i(kx+\,!\,t)}$ + cx:]=2, propagating perpendicularly to the surface of the dielectric. Here E, , !, and k = !=c are the envelope, the polarization vector, the frequency, and the wave number, respectively, of the laser eld. The eld refected from the surface is E $_2$ = R [Ee $^{i(kx-\,!\,t)}$ + cx:]=2, where R = (n_1 1)=(n_1+1) is the refection coefcient. A coording to Ref. [4], the time evolution of the density matrix of the atom is governed by the equations

$$-aa^{0} = \frac{i}{2} \frac{X}{(aba^{0}b^{0}e^{iabt})} = \frac{1}{2} (a^{+}a^{0}) aa^{0};$$

$$-ab = \frac{i}{2} \frac{X}{(ab^{0}b^{0}b^{0}e^{iab^{0}t})} = \frac{i}{2} \frac{X}{(ab^{0}a^{0}b^{0}b^{0}e^{iab^{0}t})} = \frac{1}{2} aab;$$

$$-bb^{0} = \frac{i}{2} \frac{X}{(aa^{0}bb^{0} + a^{0}ab^{0}b^{0}e^{i(!_{bb^{0}}!_{aa^{0}})t})} = \frac{1}{2} \frac{X}{(aa^{0}bb^{0} + a^{0}ab^{0}b^{0})} = \frac{1}{2} \frac{X}{(aa^{0}b^{0} + aa^{0}b^{0} + aa^{0}b^{0})} = \frac{1}{2} \frac{X}{(aa^{0}b^{0} + aa^{0}b^{0} + aa^{0}b^{0})} = \frac{1}{2} \frac{X}{(aa^{0}b^{0} + aa^{0}b^{0} + aa^{0}b^{0} + aa^{0}b^{0})} = \frac{1}{2} \frac{X}{(aa^{0}b^{0} + aa^{0}b^{0} + aa^{0}b^{0} + aa^{0}b^{0} + aa^{0}b^{0} + aa^{0}b^{0})} = \frac{1}{2} \frac{X}{(aa^{0}b^{0} + aa^{0}b^{0} + aa^{$$

where the parameters $_{aa}{}^{0}bb^{0}$ and $_{a}$ $_{b}$ $_{aabb}$ are the radiative decay coe cients [4], the index l=1 or 2 labels the incident or rejected eld, respectively, the notation $_{ab}=!$ $!_{a}+!_{b}$ stands for the detuning of the eld frequency! from the atom ic transition frequency $!_{ab}=!_{a}$ $!_{b}$, and the quantities

$$_{1ab} = F_{ab}(k) = F_{ab}(k);$$
 $_{2ab} = R F_{ab}(k)$ (3)

are the R abi frequencies of the elds E $_{\rm l=1;2}$ with respect to the translational-state transition a \$ b. Here, = Ed $_{\rm eg}$ =h is the R abi frequency of the driving eld with respect to the transition between the internal states jei and jgi, with d $_{\rm eg}$ = hejljgi being the projection of

the atom ic dipole m om ent onto the polarization vector . The coe cient

$$F_{ab}(k) = h'_{a} \dot{p}^{ikx} \dot{J}_{b} \dot{i}$$
 (4)

is the overlapping m atrix element that characterizes the transition between the center-of-m ass states j a i and j b i w ith a transferred m omentum of hk. Since ' a and ' b are real functions, we have F_{ab} (k) = F_{ab} (k). In deriving Eqs. (3), we have neglected the cross decay coe cients aa^0 b aa^0bb with a abla a. Such coe cients are small compared to the radiative linewidths a and a^0 when the refractive index a1 of the dielectric is not large [4].

We plot in Fig. 2 the Frank (Condon factors $\mathcal{F}_{ab}(k)$) for three bound ground-state levels $\,_{\mathrm{b}}$ and various bound excited-state levels a. As seen from the gure, a deep bound ground-state level can be substantially coupled to a deep excited-state level. A deeper lower level can substantially overlap with a deeper upper level. The level $_{\rm b} = 285$, with translational energy shift $E_{\rm b} =$ M Hz, can be substantially coupled to the level $_{\rm a}$ = 400, with translational energy shift $E_a =$ 132:84 M Hz. The di erence Ea $E_b = 78.45 \text{ M} \text{ Hz}$ is negative and large compared to the natural linewidth $_0 = 5.25 \text{ MHz}$ of the D₂ line of atom ic cesium. In principle, both types of shifts, namely red (negative) shifts (E_a E_b < 0) and blue (positive) shifts (Ea $E_0 > 0$), of the transition frequencies m ay be obtained. Note that the van der W aals potential for the excited state is stronger than that for the ground state. Therefore, for a bound-to-bound transition with a substantial Frank (Condon factor, the energy shift of the excited-state level is usually larger than that of the ground-state level. Consequently, the strong boundto-bound transitions usually have red shifts. Since the depths of the surface-induced potentials V_q and V_e are large (159.6 THz for V_q and 316 THz for V_e), the range of the frequency shifts of the strong bound-to-bound transitions is broad, and the shifts can reach large negative values.

We plot in Fig. 3 the Frank (Condon factors $\mathcal{F}_{ab_f}(k)$) for a free ground-state levelb, and various bound excitedstate levels a. The gure shows that the values of the Frank {C ondon factors $f_{ab_f}(k)$ } are m ore substantial for shallow bound excited-state levels than for deep ones. Am ong the bound excited-state levels, the level that is m ost strongly coupled to the free ground-state level bf is the level with the quantum number a = 415. The translational energy shift of this level is $E_a = 6.56 \,\mathrm{M}\,\mathrm{Hz}$. This bound level of the excited state is rather shallow. Due to this fact, the frequency shift Ea $\mathbf{E}_{\!\!\!D_{\mathrm{f}}} =$ MHz of the strongest free-to-bound transition from the free level $E_{b_f} = 4.25 \text{ M} \text{ Hz}$ is negative but not large. W e note that, when the temperature of the atom ic system is low, the typical values of the free-level energy $E_{b_{\epsilon}}$ are small. In this case, the range of the frequency shifts of substantial free-to-bound transitions is small compared to the range of the frequency shifts of substantial boundto-bound transitions.

We now calculate the excitation spectrum of the atom

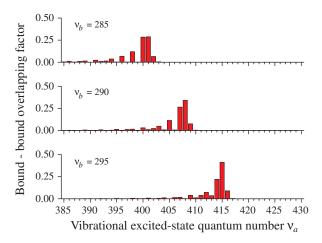


FIG. 2: Frank{C ondon factors $\mathbf{F}_{ab}(\mathbf{k})\hat{\mathbf{f}}$ for three bound ground-state levelsb, with $_b=285,290$, and 295, and various bound excited-state levels a, with $_a$ in the range from 385 to 430. The light wavelength is =852 nm. O ther param eters are as in Fig. 1.

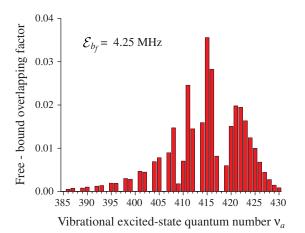


FIG. 3: Frank{C ondon factors \mathfrak{F}_{ab_f} (k) \mathring{f} for a free ground-state level b_f , with $E_{b_f}=4.25$ MHz, and various bound excited-state levels a, with $_a$ in the range from 385 to 430. The parameters used for calculations are as in Fig. 2.

in the surface-induced potential. A ssum e that the eld is so weak that the R abi frequency is much smaller than the natural linew idth $_0$. We also assume that the atom is initially in a coherent mixtures of the ground-state levels b with the weight factors $_{\rm hb} = _{\rm hb} (0)$, which are the initial populations of the levels. We consider the adiabatic regime. We not from Eqs. (2) that the population as of the excited-state level a is given by

$$_{aa} = \frac{s}{2} \sum_{b}^{X} \frac{{}^{2}_{0}}{{}^{2}_{a} + 4 {}^{2}_{ab}} \mathcal{F}_{ab}(k) \qquad R \, \mathcal{F}_{ab}(k) \, \mathcal{J}_{bb}; \qquad (5)$$

where $s = 2j j^2 = \frac{2}{0}$ is the saturation parameter. The rate of total scattering of light from the atom is given by

$$SC = \sum_{a=a}^{P} a_{aa} a. W \text{ ith the help of Eq. (5), we nd}$$

$$SC = \frac{s}{2} \frac{X}{ab} \frac{\frac{2}{a^2 + 4} \frac{2}{ab}}{\frac{2}{a^2 + 4} \frac{2}{ab}} a F_{ab} (k) R F_{ab} (k) f_{bb}^2 (k)$$
 (6)

We note that, due to the presence of the interface, the eld in a mode can be either a propagating light wave or a bound evanescent wave [15, 16]. An evanescent wave appears on the vacuum side of the interface when a light beam passing from the dielectric to the vacuum is totally internally rejected. Therefore, we can decompose the spontaneous emission rate as $_{a}=_{a}^{(ev)}+_{a}^{(rad)}$, where $_{a}^{(ev)}$ and $_{a}^{(rad)}$ are the rates of spontaneous emission from the levela into the bound evanescent modes and the propagating radiation modes, respectively [4]. Hence, we have $_{sc}=_{sc}^{(ev)}+_{sc}^{(rad)}$, where

$${}_{sc}^{(ev)} = \frac{s}{2} \frac{X}{{}_{ab}} \frac{{}_{0}^{2}}{{}_{a}^{2} + 4 {}_{ab}^{2}} {}_{a}^{(ev)} \mathcal{F}_{ab}(k) \qquad R F_{ab}(k) \mathcal{J}_{bb};$$
(7)

is the rate of scattering from the atom into the evanescent m odes and $_{\rm sc}^{\rm (rad)} = _{\rm sc}^{\rm (ev)}$ is the rate of scattering from the atom into the propagating radiation m odes.

A lithe above results were derived for a two-level atom moving in a potential induced by an in nite at surface, and Eqs. (6) and (7) represent the rigorous expressions for the rates of the total scattering and the scattering into the evanescent modes (in the fram ework of the adiabatic approximation and the perturbation theory). However, with a proper assessment of the limitations, the above theory can be applied to typical experim ental situations. As an example, we pick a recent experiment [3], whereby, the number of photons scattered from cesium atoms into the guided modes of a nano berwasmeasured as a function of the frequency of the probe eld. To apply our at-surface results to the situation of a nano ber, we use several assum ptions and approxim ations. First of all, we note that, in the case of an atom near a ber, the e ective potential for the center-of-m assmotion of the atom along the radial direction must include the centrifugal potential $U_{cf} = h^2 (l_r^2)$ 1=4)=2m r^2 . Here l_z is the quantum num ber for the axial component of the angular momentum of the atom. Since the van der W aals potential is $U_{
m vdW}=C_3=r^3$, we have $J\!\!\!/ U_{
m cf}J$ $J\!\!\!/ U_{
m vdW}$ jwhen the condition r r_c 2m $C_3=(h^2)J_z^2$ 1=4) is satis ed. Thus, when the atom is near to the ber surface and the axial angular m om entum is small, the e ect of the centrifugal is small compared to that of the van der W aals potential. In this case, we can neglect the centrifugal potential. For cesium atoms with m = 132.9 a.u. and l_z = 10, the condition for the validity of the above approximation is $r_c = 411 \text{ nm} \cdot \text{Next}$, we note that the rejection of an incident plane wave from a cylindrical surface is rather com plicated; it does not produce a plane wave. However, for the silica (vacuum interface, the re ection coe cient for light with wavelength = 852 nm is R = 0.18, a sm all number. Therefore, to simplify our calculations,

we can neglect the rejection of light from the ber surface. Finally, we note that there are two types of modes of the eld in the presence of a nano ber, namely guided modes and radiation modes. The guided modes are characterized by evanescent waves on the outside of the ber. They are then the direct analog of the evanescent modes of a dielectric (vacuum interface.

For a cesium atom at rest, the rate (r) of total spontaneous em ission and the rate (r) of spontaneous em ission into the guided modes of a nano ber have been calculated system atically in Ref. [6]. For an atom in a translational state jai, the rate a of total spontaneous em ission and the rate a of spontaneous em ission into the guided modes can be estimated as [4]

We plot in Fig. 4 the rates $_{\rm a}$ and $_{\rm a}^{\rm (g)}$ for a nano ber with radius of 200 nm, which was used in the experiment [3]. Figure 4 shows that the emission into the guided modes is substantial for a wide range of bound excited-state levels ($_{\rm a}$ < 430). However, when $_{\rm a}$ is very large ($_{\rm a}$ = 430), the channeling of emission into the guided modes becomes negligible. The reason is that, when $_{\rm a}$ is very large the bound state is very shallow. The atom in such state spends most of its time far away from the surface, where the evanescent waves in the guided modes cannot penetrate into.

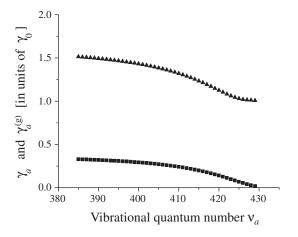


FIG. 4: Rate of total spontaneous em ission, a (triangles), and rate of spontaneous em ission into the guided m odes, a (quadrates), for a nano ber. The parameters for the surface (atom potentials are as in Fig. 1. The atom ic transition wavelength is $_0=852\ \text{nm}$. The ber radius is 200 nm . All the rates are averaged with respect to the orientation of the dipole moment.

W ith the above simplications and approximations, the rate of scattering into the guided modes of a nanober

can be estim ated by

The dependence of $_{\rm SC}^{(g)}$ on the eld{atom detuning = ! !0 (the di erence between the probe eld frequency ! and the free-space atom ic resonance frequency !0) characterizes the optical excitation spectrum of the atom in the surface-induced potential. We calculate $_{\rm SC}^{(g)}$ for two cases. In the rst case, the atom is initially in free ground-state levels. In the second case, the atom is initially in bound ground-state levels. We plot the results for the rst and second cases in Figs. 5 and 6, respectively.

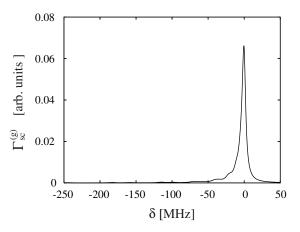


FIG. 5: Rate $^{(g)}_{sc}$ of light scattering from the atom into the guided modes of a nano ber through the free-to-bound transitions as a function of the detuning = ! ! 0 of the probe eld. The atom is initially in a therm alm ixture of free ground states with temperature T = 200 K. The range of the quantum numbers a of the bound excited states involved into the calculations is from 385 to 429. The natural linewidth of the atom is 0 = 525 MHz. Other parameters are as in Figs. 1 and 4.

In the rst case, i.e. the case of Fig. 5, we assume that the initial state of the atom is a thermal mixture of free ground states p_f i, described by the density operator

$$(0) = \text{ jgihgj} \quad P_E \neq \text{ ihE jdE} :$$
 (10)

Here, E i are the continuum eigenstates, normalized to the delta function of energy, for the ground-state H am iltonian $p^2=2m+V_g$ (r), and $P_E=e^{E=k_BT}=\!\!Z$ is the Boltzmann weight factor, with T and Z being the temperature and partition function, respectively, for the atom ic system. The dependence of the scattering rate $^{(g)}_{sc}$ on the eld detuning in Fig. 5 represents the optical excitation spectrum for the atom ic free-to-bound transitions. This spectrum shows a small negative shift of about $0.4\,\mathrm{M}$ Hz for the position of the peak. The linewidth of the spectrum is about $6.7\,\mathrm{M}$ Hz, slightly larger than the natural

linew idth $_0 = 5.25 \,\mathrm{M}\,\mathrm{Hz}$ of the D $_2$ line of atom ic cesium. In addition, the spectrum has a small, short tail on the negative side of the detuning. These features are the results of the negative frequency shifts of the transitions between free ground-state levels and bound excited-state levels. The observed e ects are however weak, and the excitation spectrum is basically concentrated around the atom ic resonance frequency ! 0. The reason is the follow ing: The Frank (Condon factor for the overlap between a free ground-state and a deep bound excited-state level is small (see Fig. 3). Therefore, a free ground-state atom can be excited only to shallow bound levels (and free levels) of the excited state. M eanwhile, an atom in a shallow (or free) excited level cannot em it photons e ciently into the guided modes because the atom spends most of its time far away from the ber (see Fig. 4). Hence, the e ect of the surface-induced potential on the excitation spectrum in the case of free-to-bound transitions is rather weak.

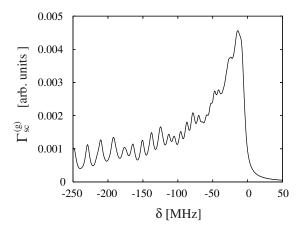


FIG. 6: Rate $^{(g)}_{sc}$ of light scattering from the atom into the guided modes of a nano ber through the bound-to-bound transitions as a function of the detuning = ! ! 0 of the probe eld. The atom is initially in an incoherent mixture of a number of bound ground-state levels with quantum numbers b from 269 to 293 and equal weight factors. The bound excited-state levels involved into the calculations are those with the quantum numbers a from 385 to 429. The natural linewidth of the atom is 0 = 525 MHz. O ther parameters are as in Figs. 1 and 4.

In the second case, i.e. the case of Fig. 6, we assume that the initial state of the atom is in an incoherent mixture of a number of bound ground-state levels $_{\rm b}$, with at weight factors $_{\rm bb}$ = const. The initial density operator of the atom is given by

$$(0) = \frac{1}{N} \qquad \text{be min}$$
 points; (11)

where N is the number of bound ground-state levels involved in the initial state of the atom. The use of at weight factors is explained by the assumption that the

atom is adsorbed by a surface at the room temperature T = 300 K = 6.25 THz, which is much higher than the energy di erences between the levels. For our num erical calculations, we include the bound ground-state levels with quantum numbers b from 269 to 293. The energy shifts of these levels, equal to their total center-of-m ass energies, are in the range from 1 GHzto 5 M Hz. W e do not include levels with larger quantum numbers because they are too shallow and therefore, an atom in such a bound ground-state level can be easily excited to a free ground-state level by heating or collision. We also do not include levels with smaller quantum numbers because the corresponding transition frequency shifts are beyond the range of the excitation spectrum measured in the experim ent [3]. The dependence of the scattering rate on the eld detuning in Fig. 6 represents the optical excitation spectrum for the atom ic bound-to-bound transitions. This spectrum shows a substantial negative shift of about 143 MHz for the position of the peak. The linewidth of the spectrum is about 58.3 MHz, which is one order larger than the natural linew idth $_0 = 5.25$ MHz of the D $_2$ line of atom ic cesium. Furtherm ore, the spectrum has a substantial long tail on the negative side and a small short tail on the positive side of the detuning. These features are the results of the frequency shifts of the transitions between bound ground-state levels and bound excited-state levels. In general, both negative and positive shifts can come into play. However, the transitions with positive shifts are relatively weak because the corresponding Frank (Condon factors are usually small. The overlap between the center-of-mass wave functions of a bound excited-state level and a bound ground-state level is substantial only when the corresponding returning points are close to each other. Since the van der W aals potential for the excited state jei is deeper than that for the ground state jgi, the frequency shifts of the transitions that are associated with substantial Frank { Condon factors are mostly negative. The deeper the bound ground-state levels involved in the initial state, the stronger the e ect of the surface (atom interaction on the excitation spectrum. We note that the basic features of the spectrum in Fig. 6 are very similar to the features of the right and left wings of the experimental spectrum reported in Ref. [3]. However, it is important to recall that the experim ental spectrum [3] has contributions from both bound-to-bound and free-to-bound types of transitions. A combination of both Figs. 5 and 6 with proper weight factors can indeed lead to an excellent m atching of the experim ental spectrum with the theoretically predicted one.

In conclusion, we have studied the optical excitation spectrum of an atom in the vicinity of a dielectric surface. We have derived rigorous expressions for the rates of the total scattering and the scattering into the evanescent modes. We ith a proper assessment of the limitations, our theoretical results have been applied to an experimental situation with a nano ber. We have shown that the elect of the surface-induced potential on the excitation spec-

trum in the case of free-to-bound transitions is rather weak. Meanwhile, the spectrum of excitation of bound-to-bound transitions has a large linewidth, a substantial negative shift of the peak position, and a substantial long tailon the negative side and a small short tailon the positive side of the eld (atom frequency detuning. The basic features of the calculated spectra are in agreement with the experimental observations [3].

A cknow ledgm ents

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